Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 60 A



www.vishay.com

SOT-227

PRODUCT SUMMARY						
V _R	600 V					
V _F (typical) at 125 °C	1.4 V					
Q _{rr} (typical)	270 nC					
I _{RRM} (typical)	7.0 A					
t _{rr} (typical)	65 ns					
dl _{(rec)M} /dt (typical) at 125 °C	270 A/µs					
$I_{F(DC)}$ at T_C	40 A at 100 °C					
Package	SOT-227					
Circuit configuration	Two separate diodes					

FEATURES

- Fast recovery time characteristic
- Electrically isolated base plate
- Large creepage distance between terminal
- Simplified mechanical designs, rapid assembly
- UL approved file E78996
- Designed for industrial level
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

This SOT-227 modules with HEXFRED® rectifier are available in two basic configurations. They are the antiparallel and the parallel configurations. The antiparallel configuration (VS-HFA120EA60) is used for simple series rectifier and high voltage application. The parallel configuration (VS-HFA120FA60) is used for simple parallel rectifier and high current application. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built. These modules are intended for general applications such as power supplies, battery chargers, electronic welders, motor control, DC chopper, and inverters.

ABSOLUTE MAXIMUM RATINGS PER LEG						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		600	V		
Continuous forward current		T _C = 25 °C	75			
Continuous forward current	١ _F	T _C = 100 °C	40	٨		
Single pulse forward current	I _{FSM}	$T_J = 25 \ ^{\circ}C$	800	A		
Maximum repetitive forward current	I _{FRM}	Rated V _R , square wave, 20 kHz, $T_C = 60 \degree C$	180			
RMS isolation voltage, any terminal to case	VISOL	t = 1 minute	2500	V		
Maximum power dissipation	р	T _C = 25 °C	180	W		
Maximum power dissipation	P _D	T _C = 100 °C	71	vv		
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to 150	°C		

ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA		600	-	-		
	V _{FM}	I _F = 60 A	See fig. 1	-	1.5	1.7	V	
Maximum forward voltage		I _F = 120 A		-	1.9	2.1		
		I _F = 60 A, T _J = 125 °C		-	1.4	1.6		
Maximum reverse leakage current	I _{RM}	$V_R = V_R$ rated	See fig. 2	-	2.5	20		
Maximum reverse leakage current		T_J = 125 °C, V_R = 0.8 x V_R rated	See fig. 2	-	130	2000	μA	
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	120	170	pF	

Revision: 22-Jul-13

1

Document Number: 94049

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



COMPLIANT

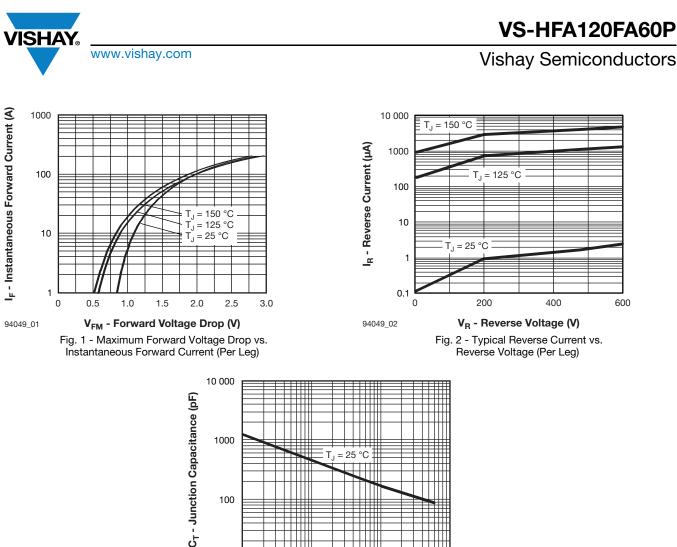


www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS PER LEG ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONE	DITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	I _F = 1.0 A, dI _F /dt = 200 A	õs, V _R = 30 V	-	34	-		
Reverse recovery time See fig. 5, 6 and 16	t _{rr1}	T _J = 25 °C		-	65	98	ns	
	t _{rr2}	T _J = 125 °C	I _F = 60 A dI _F /dt = 200 A/μs	-	130	200		
Peak recovery current See fig. 7 and 8	I _{RRM1}	T _J = 25 °C		-	7.0	13	А	
	I _{RRM2}	T _J = 125 °C		-	13	23	~	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	$V_{\rm B} = 200 \text{ V}$	-	270	410	nC	
See fig. 9 and 10	Q _{rr2}	T _J = 125 °C		-	490	740	no	
Peak rate of recovery current during t_b	dl _{(rec)M} /dt1	T _J = 25 °C		-	350	-	A∕µs	
See fig. 11 and 12	dl _{(rec)M} /dt2	T _J = 125 °C		-	270	-	λγμs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Junction to case, single leg conducting	- R _{thJC}		-	-	0.70		
Junction to case, both legs conducting	nthJC		-	-	0.35	°C/W	
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.05	-		
Weight			-	30	-	g	
Mounting torque			-	-	1.3	Nm	
Case style			SOT-227				



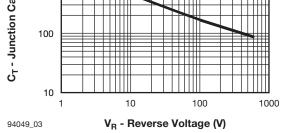
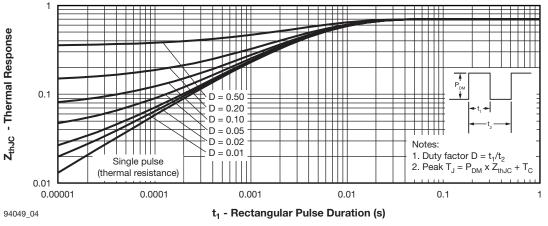


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)





Revision: 22-Jul-13

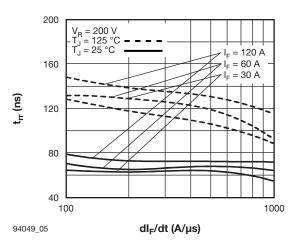
3

Document Number: 94049

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

VS-HFA120FA60P

Vishay Semiconductors



www.vishay.com

ISHAY

Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

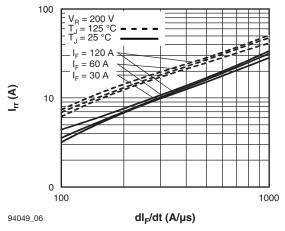
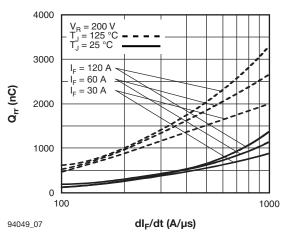


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)





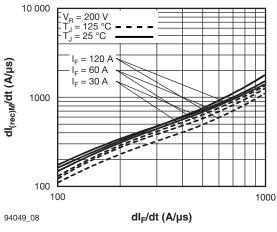


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

VS-HFA120FA60P

Vishay Semiconductors



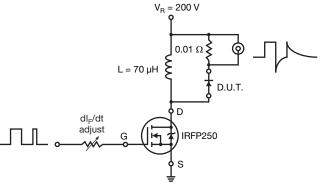


Fig. 9 - Reverse Recovery Parameter Test Circuit

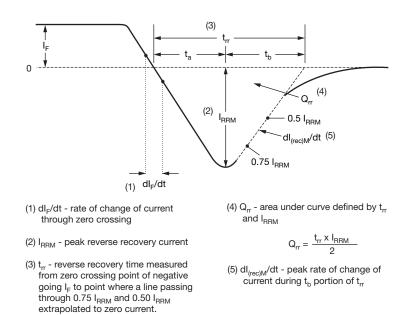


Fig. 10 - Reverse Recovery Waveform and Definitions

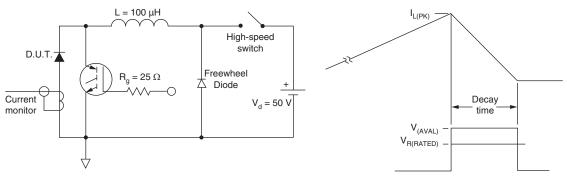


Fig. 11 - Avalanche Test Circuit and Waveforms

Revision:	22-Jul-13
-----------	-----------

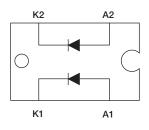
For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay Semiconductors



CIRCUIT CONFIGURATION



ORDERING INFORMATION TABLE

Device code

VS-	HF	A	120	FA	60	Ρ		
	2	3	4	5	6	(7)		
Vishay Semiconductors product								
2	- HE	HEXFRED [®] family						
3	- Pro	Process: A electron irradiated						
4	- Cu	Current rating (120 = 120 A)						
5	- Pa	Package indicator (SOT-227)						
6	- Vol	Voltage rating (60 = 600 V)						
7	- P=	P = Lead (Pb)-free						

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95036						
Packaging information	www.vishay.com/doc?95037					

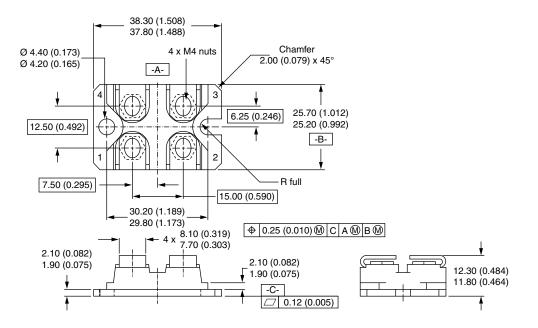


Outline Dimensions

Vishay Semiconductors

SOT-227

DIMENSIONS in millimeters (inches)



Notes

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.